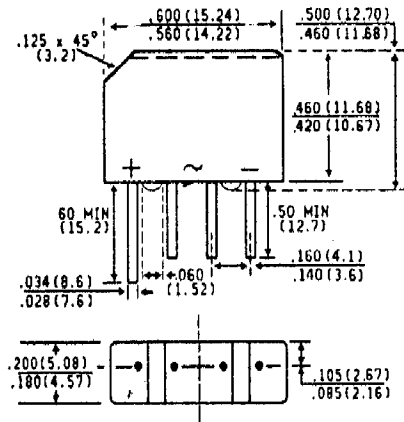


## 3N253 THRU 3N259

MINIATURE GLASS PASSIVATED SINGLE - PHASE SILICON BRIDGE RECTIFIER  
VOLTAGE - 50 to 1000 Volts CURRENT - 2.0 Amperes

### FEATURES



Dimensions in inches  
and  
millimeters

### MECHANICAL DATA

**Case:** Reliable low cost construction utilizing molded plastic technique

**Terminals:** Plated Lead solderable per MIL-STD-202, Method 208

**Mounting position:** Any

**Weight:** 0.06 ounce, 1.70 grams

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.  
60 Hz Resistive or inductive load.

	SYMBOLS	3N253	3N254	3N255	3N256	3N257	3N258	3N259	UNITS
* Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	Volts
* Maximum RMS Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	Volts
* Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	Volts
* Maximum Average Forward Output Rectified Current at T <sub>A</sub> = 55°C	I <sub>(AV)</sub>				2.0				Amps
* Peak Forward Surge Current Single sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>				60.0				Amps
Rating for fusing (t < 8.35ms)	I <sub>t</sub>				15.0				A <sup>2</sup> s
* Maximum Instantaneous Forward Voltage drop per element at 3.14A	V <sub>F</sub>				1.1				Volts
* Maximum DC Reverse Current T <sub>A</sub> = 25°C at Rated DC Blocking Voltage per element T <sub>A</sub> = -125°C	I <sub>R</sub>				10.0				μA
Typical Junction Capacitance per element (Note 1)	C <sub>J</sub>				25.0				pf
Typical Thermal Resistance (Note 2)	R <sub>θJA</sub>				30.0				°C/W
* Operating and Storage Temperature Range,	T <sub>J</sub> , T <sub>STG</sub>				-55 to +165				°C



Quality Semi-Conductors